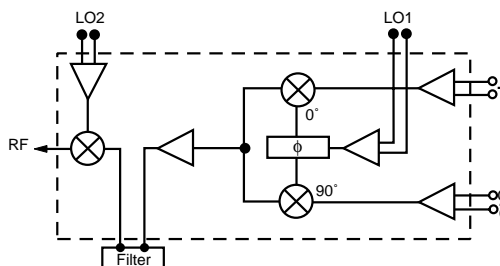


### FEATURES

- **WIDE SUPPLY VOLTAGE RANGE:** 2.7 ~ 5.5 V
- **BROADBAND OPERATION:** RF<sub>OUT</sub> = 0.8 - 2.4 GHz  
MOD<sub>OUT</sub> = 100 - 400 MHz, I/Q = DC to 10 MHz
- **INTERNAL 90° PHASE SHIFTER**
- **PORTS FOR EXTERNAL IF FILTER**
- **LOW POWER CONSUMPTION:** 28 mA AT 3 VOLT TYPICAL
- **SMALL SSOP 20 PACKAGE**
- **TAPE AND REEL PACKAGING AVAILABLE**

### FUNCTIONAL BLOCK DIAGRAM



### DESCRIPTION

The UPC8104GR Silicon MMIC Frequency Upconverter with I/Q Modulator is manufactured using the NESAT III MMIC process. The NESAT III process produces transistors with  $f_T$  approaching 20 GHz. The device was designed for use in 800 MHz to 2.4 GHz Digital Mobile Communications circuits such

as 900 MHz Digital Cordless Phones, WLAN and PCN/PCS Handset Transmitters.

NEC's stringent quality assurance and test procedures ensure the highest reliability and performance.

### ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C, V<sub>CC</sub> = 3.0 V, V<sub>PS</sub> ≥ 1.8 V)

		PART NUMBER PACKAGE OUTLINE			UPC8104GR S20 (SSOP 20)		
SYMBOLS		PARAMETERS AND CONDITIONS		UNITS	MIN	TYP	MAX
Total	I <sub>CC</sub>	Total Circuit Current (no signal)	V <sub>PS</sub> ≥ 1.8 V V <sub>PS</sub> ≤ 1.0 V	mA μA	18	28 0.1	37 10
	PRF	Total Output Power <sup>1,2</sup>		dBm	-18.5	-13.5	-8.5
	LOL	Upconverter LO Carrier Leakage <sup>1</sup>		dBc		-40	-30
	ImR	Image Rejection <sup>1</sup> (Side Band Leakage)		dBc		-40	-30
Up Converter	I <sub>CC</sub>	Circuit Current - Upconverter (no signal)	V <sub>PS</sub> ≥ 1.8 V V <sub>PS</sub> ≤ 1.0 V	mA μA		12	5
	CG	Conversion Gain <sup>1</sup>	f <sub>RF</sub> = 900 MHz, f <sub>IF</sub> = 240 MHz, f <sub>LO</sub> = 1140 MHz f <sub>RF</sub> = 1900 MHz, f <sub>IF</sub> = 240 MHz, f <sub>LO</sub> = 1660 MHz f <sub>RF</sub> = 2450 MHz, f <sub>IF</sub> = 240 MHz, f <sub>LO</sub> = 2210 MHz	dB dB dB		10 4.5 4	
	PRF (SAT)	Maximum Output Power - Upconverter	f <sub>RF</sub> = 900 MHz, f <sub>IF</sub> = 240 MHz f <sub>RF</sub> = 1900 MHz, f <sub>IF</sub> = 240 MHz	dBm dBm		-2 -6	
	OIP <sub>3</sub>	Output 3rd Order Intercept Point	f <sub>RFOUT</sub> = 1.9 GHz f <sub>IF</sub> = 240.0 MHz/240.2 MHz	dBm		0	
Modulator	I <sub>CC</sub>	Circuit Current - Modulator (no signal)	V <sub>PS</sub> ≥ 1.8 V V <sub>PS</sub> ≤ 1.0 V	mA μA	10	16	21 5
	P <sub>MOD</sub>	Output Power - Modulator <sup>2</sup>		dBm		-17.5	
	LOLEAK	Local Oscillator Leakage <sup>2</sup>		dBc		-40	-30
	ImR	Image Rejection <sup>2</sup>		dBc		-40	-30
	IM <sub>3</sub> I/Q	I/Q 3rd Order Intermodulation Distortion <sup>2</sup>		dBc		-50	
	RLIN	I/Q LO Input Return Loss		dB		20	
	Z <sub>I/Q</sub>	Input Impedance I and Q Ports <sup>2</sup>		kΩ		20	
	I <sub>I/Q</sub>	I/Q Bias Current		μA		5	
	T <sub>PS</sub> (RISE)	Power Save Rise Time	V <sub>PS</sub> ≤ 1.0 V to V <sub>PS</sub> ≥ 1.8 V	μS		2.0	5.0
	T <sub>PS</sub> (FALL)	Power Save Fall Time	V <sub>PS</sub> ≥ 1.8 V to V <sub>PS</sub> ≤ 1.0 V	μS		2.0	5.0

Notes:

1. P<sub>IFIN</sub> = -20 dBm
2. V<sub>I/Q</sub> = 1.5 V (DC) +0.5 V<sub>p-p</sub> (AC)

**ABSOLUTE MAXIMUM RATINGS<sup>1</sup>** (T<sub>A</sub> = 25°C)

SYMBOLS	PARAMETERS	UNITS	RATINGS
V <sub>CC</sub>	Supply Voltage	V	6.0
V <sub>PS</sub>	Enable Voltage for Power Save	V	6.0
P <sub>D</sub>	Power Dissipation <sup>2</sup>	mW	530
T <sub>OP</sub>	Operating Temperature	°C	-40 to +85
T <sub>STG</sub>	Storage Temperature	°C	-65 to +150

Notes:

1. Operation in excess of any one of these parameters may result in permanent damage.
2. Mounted on a 50x50x1.6 mm epoxy glass PWB (T<sub>A</sub> = 85°C).

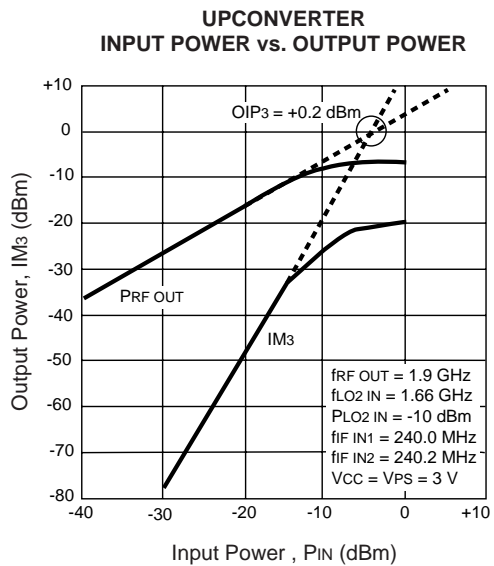
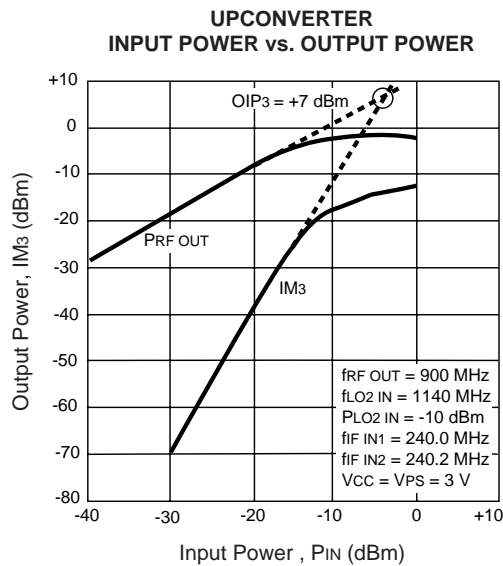
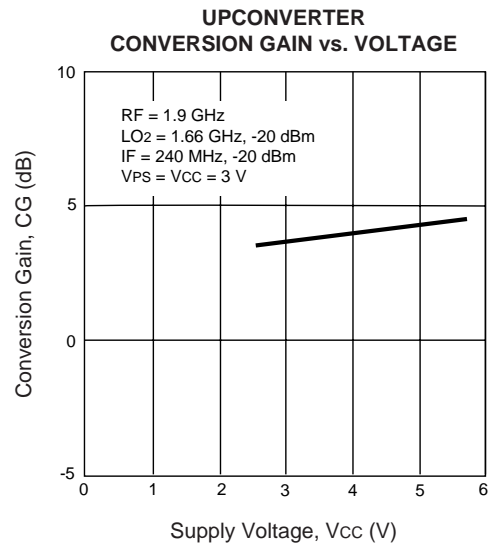
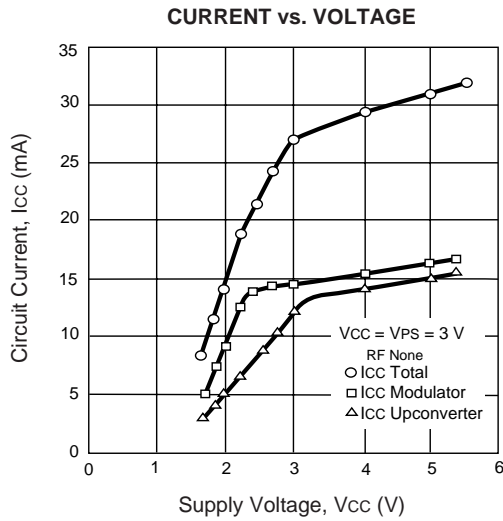
**RECOMMENDED OPERATING CONDITIONS**

SYMBOLS	PARAMETERS	UNITS	MIN	TYP	MAX
V <sub>CC</sub>	Supply Voltage	V	2.7	3.0	5.5
T <sub>OP</sub>	Operating Temperature	°C	-40	+25	+85
f <sub>RF</sub>	Up Converter RF Frequency	GHz	0.9		2.4
f <sub>IF</sub>	IF Frequency <sup>1</sup>	MHz	100		400
f <sub>LO2</sub>	Up Converter LO Frequency	GHz	0.9		2.2
f <sub>I/Q</sub>	I/Q Input Frequency <sup>2</sup>	MHz	DC		10

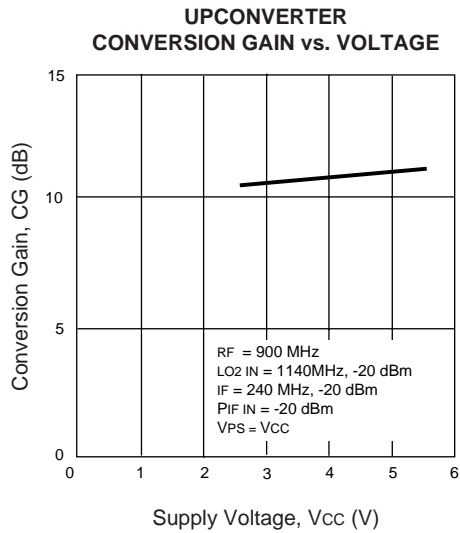
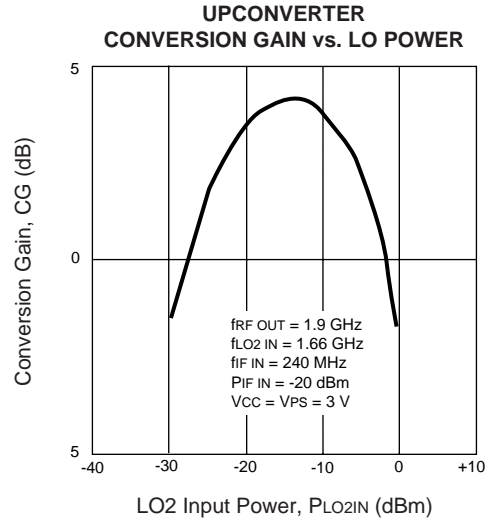
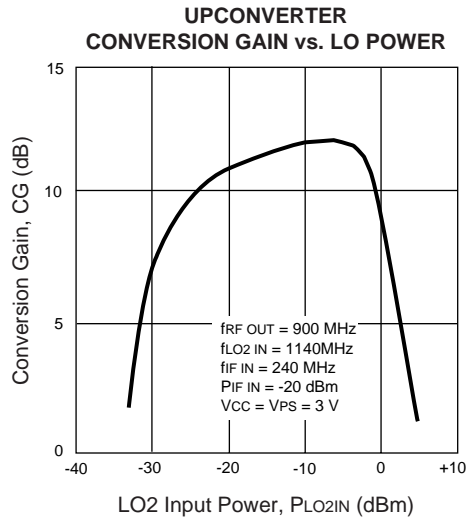
Notes:

1. IF frequency range includes Up-Converter IF input, Modulator IF Output and Modulator LO Input Frequency (LO1).
2. V<sub>I/QIN</sub> = 600 mVp-p maximum.

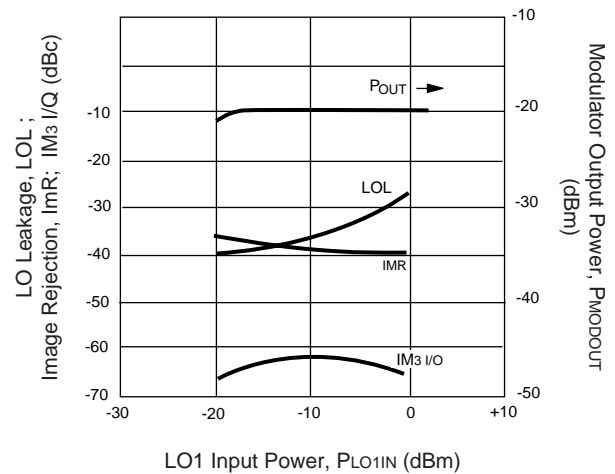
**TYPICAL PERFORMANCE CURVES** (T<sub>A</sub> = 25°C, V<sub>CC</sub> = V<sub>PS</sub> = 3 V, I/Q DC Offset =  $\overline{I/Q}$  DC Offset = 1.5 V, I/Q Input Signal = 500 mVp-p (Single Ended), P<sub>LO1IN</sub> = -10 dBm, P<sub>LO2IN</sub> = -10 dBm unless otherwise specified)



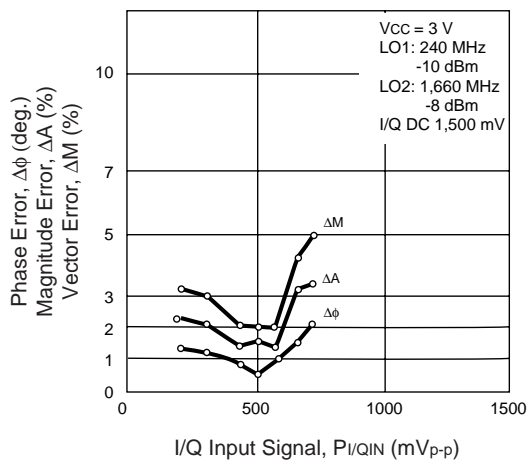
TYPICAL PERFORMANCE CURVES (TA = 25°C)



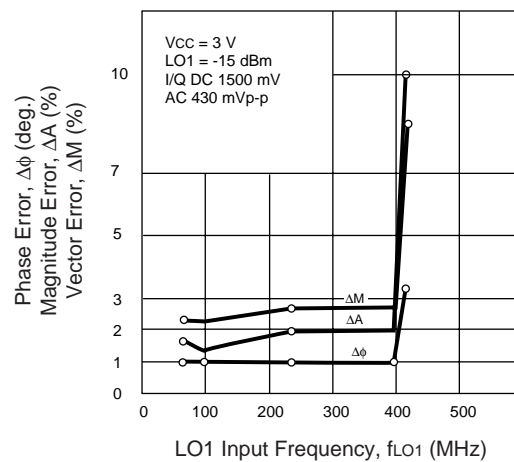
**MODULATOR  
OUTPUT POWER, LO LEAKAGE , IMAGE REJECTION  
AND I/Q 3rd ORDER INTERMODULATION DISTORTION  
vs. LO1 INPUT POWER**



**VECTOR ERROR, MAGNITUDE ERROR,  
PHASE ERROR vs. I/Q INPUT SIGNAL**

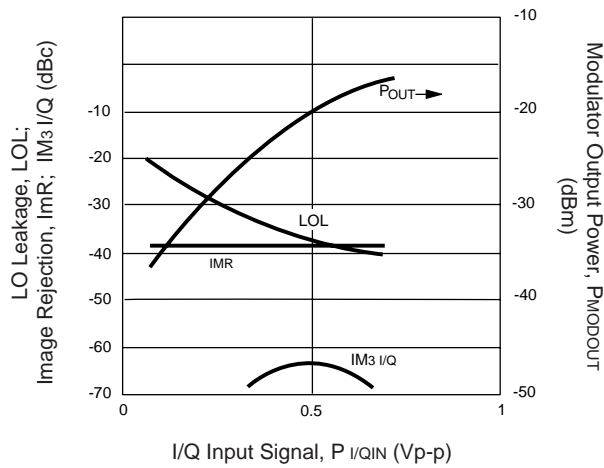


**VECTOR ERROR, MAGNITUDE ERROR,  
PHASE ERROR vs. LO1 INPUT FREQUENCY**

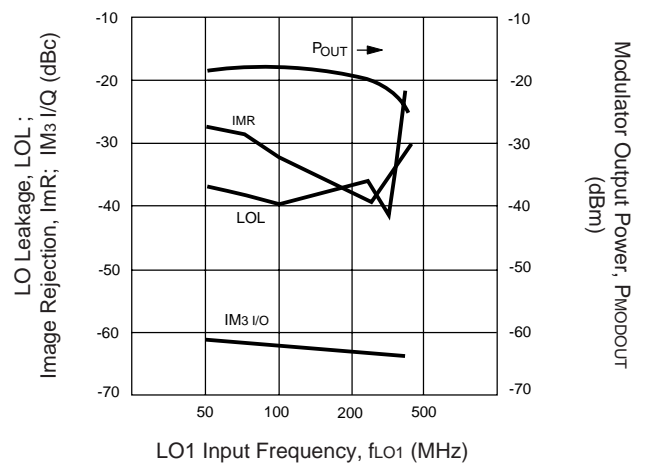


TYPICAL PERFORMANCE CURVES (T<sub>A</sub> = 25°C)

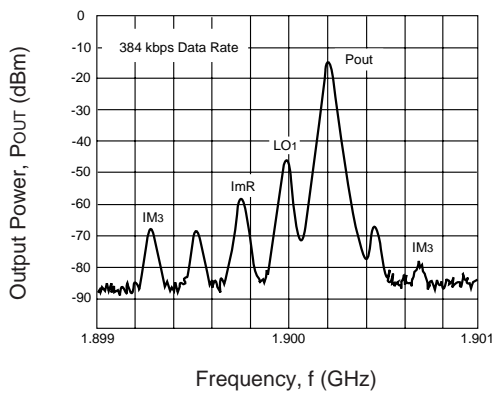
MODULATOR OUTPUT POWER, LO LEAKAGE, IMAGE REJECTION AND I/Q 3rd ORDER INTERMODULATION DISTORTION vs. I/Q INPUT SIGNAL



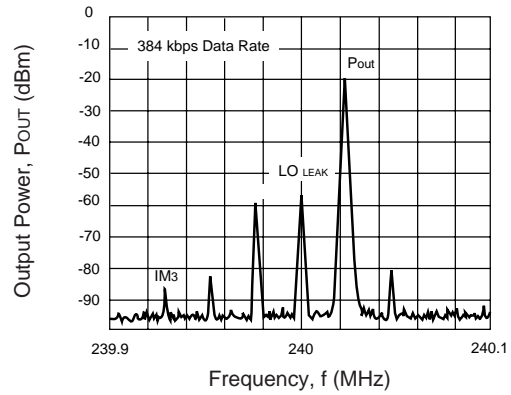
MODULATOR OUTPUT POWER, LO LEAKAGE, IMAGE REJECTION AND I/Q 3rd ORDER INTERMODULATION DISTORTION vs. LO1 INPUT FREQUENCY



MODULATOR AND UPCONVERTER TYPICAL SINE WAVE MODULATION OUTPUT SPECTRUM



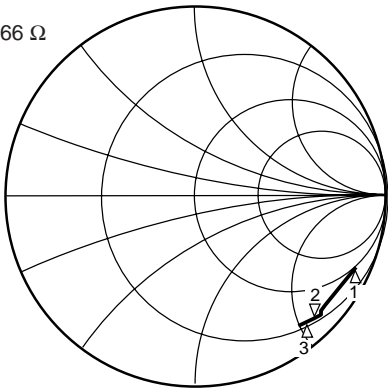
MODULATOR TYPICAL SINE WAVE MODULATION OUTPUT SPECTRUM



**TYPICAL PERFORMANCE CURVES** ( $T_A = 25^\circ\text{C}$ )

**LO2IN INPUT IMPEDANCE**

Impedance at  
Marker 2:  
 $20.184 - j113.66 \Omega$

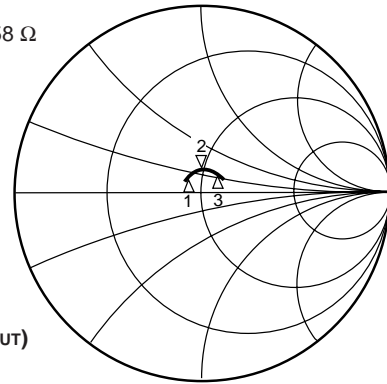


**LO2IN**  
Marker  
1. 900 MHz  
2. 1.66 GHz  
3. 1.8 GHz

Start 800 MHz  
Stop 1900 MHz

**MODOUT OUTPUT IMPEDANCE**

Impedance at  
Marker 2:  
 $49.224 - j13.58 \Omega$

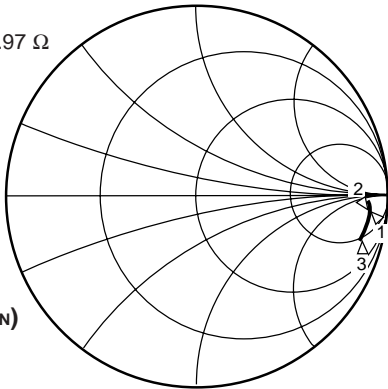


**MODOUT (IFOUT)**  
Marker  
1. 100 MHz  
2. 240 MHz  
3. 400 MHz

Start 50 MHz  
Stop 500 MHz

**Upconverter Input Impedance**

Impedance at  
Marker 2:  
 $262.19 - j394.97 \Omega$

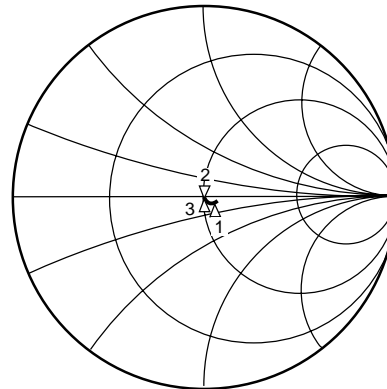


**UPCONIN (IFIN)**  
Marker  
1. 100 MHz  
2. 240 MHz  
3. 400 MHz

Start 50 MHz  
Stop 500 MHz

**LO1IN Input Impedance**

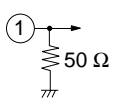
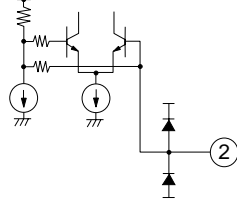
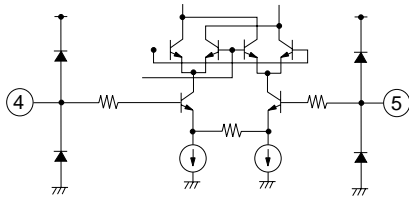
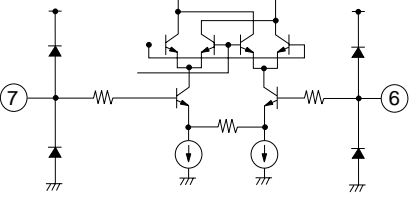
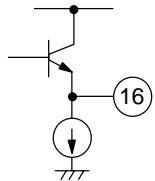
Impedance at  
Marker 2:  
 $51.727 - j2 \Omega$



**LO1IN**  
Marker  
1. 100 MHz  
2. 240 MHz  
3. 400 MHz

Start 50 MHz  
Stop 500 MHz

**PIN FUNCTIONS**

Pin No.	Symbol	Supply Voltage	Pin Voltage	Description	Equivalent Circuit								
1	LO1IN (Modulator)	—	0	LO1 input for the phase shifter. This input impedance is internally matched to 50 Ω.									
2	$\overline{\text{LO1IN}}$ (Bypass)	—		Bypass of the LO1 input. This pin is grounded through an internal capacitor. For a single-ended design this pin should be left open.									
3	GND (Modulator)			Connect to ground with minimum inductance. Track length should be kept as short as possible.									
4	I	$V_{CC/2}^{*2}$	—	Input for I signal. This input impedance is larger than 20 kΩ. The relationship between the amplitude and the DC bias of the input signal are as follows: <table border="1" data-bbox="722 682 1015 819"> <thead> <tr> <th><math>V_{CC/2}</math> (V)</th> <th>Amp. (mVp-p)<sup>*1</sup></th> </tr> </thead> <tbody> <tr> <td>≥1.35</td> <td>400</td> </tr> <tr> <td>≥1.5</td> <td>600</td> </tr> <tr> <td>≥1.75</td> <td>1000</td> </tr> </tbody> </table>	$V_{CC/2}$ (V)	Amp. (mVp-p) <sup>*1</sup>	≥1.35	400	≥1.5	600	≥1.75	1000	
$V_{CC/2}$ (V)	Amp. (mVp-p) <sup>*1</sup>												
≥1.35	400												
≥1.5	600												
≥1.75	1000												
5	$\overline{\text{I}}$	$V_{CC/2}^{*2}$	—	Input for I signal. This input impedance is larger than 20 kΩ. $V_{CC/2}$ biased DC signal should be input.									
6	$\overline{\text{Q}}$	$V_{CC/2}^{*2}$	—	Input for Q signal. This input impedance is larger than 20 kΩ. $V_{CC/2}$ biased DC signal should be input.									
7	Q	$V_{CC/2}^{*2}$	—	Input for Q signal. This input impedance is larger than 20 kΩ. The relationship between the amplitude and the DC bias of the input signal are as follows: <table border="1" data-bbox="738 1218 1031 1354"> <thead> <tr> <th><math>V_{CC/2}</math> (V)</th> <th>Amp. (mVp-p)<sup>*1</sup></th> </tr> </thead> <tbody> <tr> <td>≥1.35</td> <td>400</td> </tr> <tr> <td>≥1.5</td> <td>600</td> </tr> <tr> <td>≥1.75</td> <td>1000</td> </tr> </tbody> </table>	$V_{CC/2}$ (V)	Amp. (mVp-p) <sup>*1</sup>	≥1.35	400	≥1.5	600	≥1.75	1000	
$V_{CC/2}$ (V)	Amp. (mVp-p) <sup>*1</sup>												
≥1.35	400												
≥1.5	600												
≥1.75	1000												
16	MODOUT	—		Output from the modulator. This is emitter follower output. Connect around 15 Ω in series to match to 50 Ω.									

\*1: In case I/Q input signals are single ended. I/Q signal inputs can be used either single-ended or differentially with proper terminations.

\*2:  $V_{CC/2}$  DC bias must be supplied to I,  $\overline{\text{I}}$ , Q,  $\overline{\text{Q}}$ .

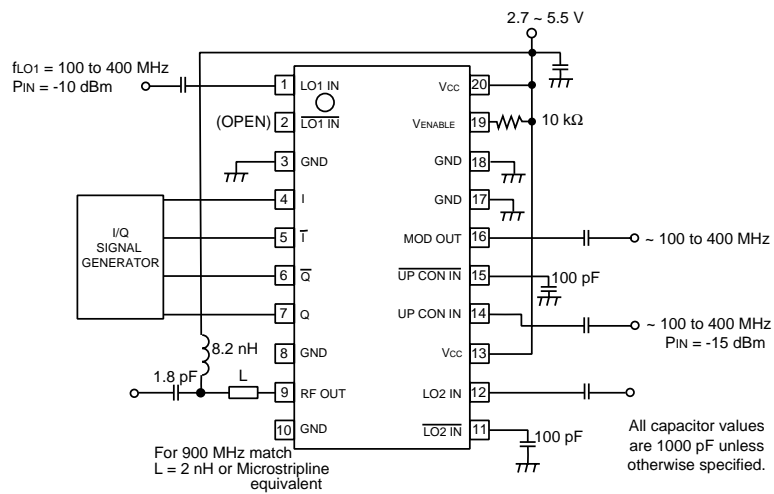
**PIN FUNCTIONS**

Pin No.	Symbol	Supply Voltage	Pin Voltage	Description	Equivalent Circuit						
8 10	GND (Upconverter)	0	-	Connect to ground with minimum inductance. Track length should be kept as short as possible.							
11	$\overline{\text{LO2IN}}$ (Bypass)	—	2.0	Bypass of the LO2 input. Requires grounding through an external capacitor.							
12	LO2IN (Upconverter)	—	0	LO2 input for the Upconverter. This pin is a high impedance input.							
13	V <sub>CC</sub> (Upconverter)	2.7~5.5	—	Supply voltage pin for the Upconverter.							
9	RF <sub>OUT</sub>	V <sub>CC</sub>	—	RF output from the Upconverter. This pin is an open collector output.							
14	Upconverter in	—	2.0	IF input for the Upconverter. This pin is a high impedance input.							
15	$\overline{\text{Upconverter in}}$ (Bypass)	—	2.0	Bypass of the IF input. Requires grounding through an external capacitor.							
17 18	GND	0	—	Connect to ground with minimum inductance. Track length should be kept as short as possible.							
19	V <sub>PS</sub> (Power Save)	V <sub>PS</sub>	—	Power save control pin can control the On/Sleep state with bias as follows: <table border="1" style="margin: 10px auto;"> <thead> <tr> <th>V<sub>PS</sub> (V)</th> <th>STATE</th> </tr> </thead> <tbody> <tr> <td>1.8~5.5</td> <td>ON</td> </tr> <tr> <td>0~1.0</td> <td>SLEEP</td> </tr> </tbody> </table>		V <sub>PS</sub> (V)	STATE	1.8~5.5	ON	0~1.0	SLEEP
V <sub>PS</sub> (V)	STATE										
1.8~5.5	ON										
0~1.0	SLEEP										
20	V <sub>CC</sub> (Modulator)	2.7~5.5	—	Supply voltage pin for the modulator. An internal regulator helps keep the device stable against temperature or V <sub>CC</sub> variation.							

**MODULATOR INTERNAL FUNCTIONS**

Block	Function/Operation	Block Diagram
90° Phase Shifter	Input signal from LO1 is sent to a T-type flip-flop through a frequency doubler. The output signal from the T-type F/F is changed to the same frequency as LO1 with a quadrature phase shift of 0°, 90°, 180°, or 270°. These circuits provide self phase correction for proper quadrature signals.	
Buffer Amplifier	Buffer amplifiers for each phase signal are sent to each mixer.	
Mixer	Each signal from the buffer amps is quadrature modulated with two double-balanced mixers. High accurate phase and amplitude inputs are realized to provide excellent image rejection.	
Adder	Output signal from each mixer is added and sent through a final amplifier stage to pin 16 for further off-chip filtering if necessary.	

**TEST CIRCUIT**

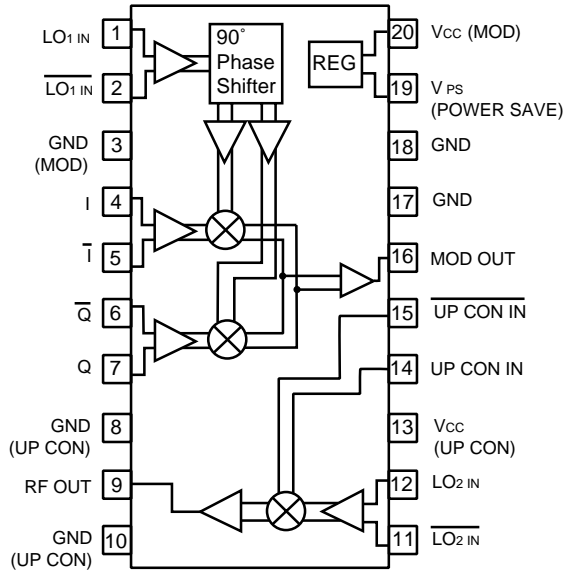


**Desired Matching Network Impedance, Based On Load Pull Measurements**

Frequency	$\Gamma_{Load} (Mag)$	$\Gamma_{Load} (Ang)$
900 MHz	0.614	67.7°
1900 MHz	0.606	169°
2450 MHz	0.318	-127°



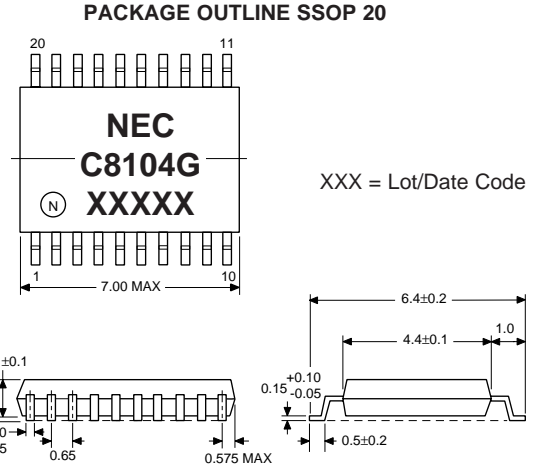
**INTERNAL BLOCK DIAGRAM**



**ORDERING INFORMATION**

PART NUMBER	QUANTITY
UPC8104GR-E1	2500/Reel

**OUTLINE DIMENSIONS** (Units in mm)



**LEAD CONNECTIONS**

- |                                   |  |
|-----------------------------------|--|
| 1. $\overline{LO1IN}$ (Modulator) | 11. $\overline{LO2IN}$ (Bypass)              |
| 2. $\overline{LO1IN}$ (Bypass)    | 12. $\overline{LO2IN}$ (Upconverter)         |
| 3. GND (Modulator)                | 13. Vcc (Up Converter)                       |
| 4. I Input                        | 14. $\overline{Up Converter Input}$          |
| 5. $\overline{I}$ Input           | 15. $\overline{Up Converter Input}$ (Bypass) |
| 6. $\overline{Q}$ Input           | 16. MOD Out                                  |
| 7. Q Input                        | 17. GND                                      |
| 8. GND (Up Converter)             | 18. GND                                      |
| 9. RF OUT                         | 19. Vps (Power Save)                         |
| 10. GND (Up Converter)            | 20. Vcc (Modulator)                          |

All dimensions are typical unless specified otherwise.

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